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What is "[Embedded - Microcontrollers](#)"?

"[Embedded - Microcontrollers](#)" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "[Embedded - Microcontrollers](#)"

Details	
Product Status	Active
Core Processor	S08
Core Size	8-Bit
Speed	20MHz
Connectivity	I ² C, LINbus, SPI, UART/USART
Peripherals	LVD, POR, PWM, WDT
Number of I/O	37
Program Memory Size	32KB (32K x 8)
Program Memory Type	FLASH
EEPROM Size	256 x 8
RAM Size	4K x 8
Voltage - Supply (Vcc/Vdd)	2.7V ~ 5.5V
Data Converters	A/D 16x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 105°C (TA)
Mounting Type	Surface Mount
Package / Case	44-LQFP
Supplier Device Package	44-LQFP (10x10)
Purchase URL	https://www.e-xfl.com/pro/item?MUrl=&PartUrl=mc9s08pt32avld

- Input/Output
 - Up to 57 GPIOs including one output-only pin
 - Two 8-bit keyboard interrupt modules (KBI)
 - Two true open-drain output pins
 - Eight, ultra-high current sink pins supporting 20 mA source/sink current
- Package options
 - 64-pin LQFP; 64-pin QFP
 - 48-pin LQFP
 - 44-pin LQFP
 - 32-pin LQFP

1 Ordering parts

1.1 Determining valid orderable parts

Valid orderable part numbers are provided on the web. To determine the orderable part numbers for this device, go to freescale.com and perform a part number search for the following device numbers: PT60 and PT32.

2 Part identification

2.1 Description

Part numbers for the chip have fields that identify the specific part. You can use the values of these fields to determine the specific part you have received.

2.2 Format

Part numbers for this device have the following format:

MC 9 S08 PT AA (V) B CC

2.3 Fields

This table lists the possible values for each field in the part number (not all combinations are valid):

Field	Description	Values
MC	Qualification status	<ul style="list-style-type: none"> MC = fully qualified, general market flow
9	Memory	<ul style="list-style-type: none"> 9 = flash based
S08	Core	<ul style="list-style-type: none"> S08 = 8-bit CPU
PT	Device family	<ul style="list-style-type: none"> PT
AA	Approximate flash size in KB	<ul style="list-style-type: none"> 60 = 60 KB 32 = 32 KB
(V)	Mask set version	<ul style="list-style-type: none"> (blank) = Any version A = Rev. 2 or later version, this is recommended for new design

Table continues on the next page...

Field	Description	Values
B	Operating temperature range (°C)	<ul style="list-style-type: none"> • V = -40 to 105
CC	Package designator	<ul style="list-style-type: none"> • QH = 64-pin QFP • LH = 64-pin LQFP • LF = 48-pin LQFP • LD = 44-pin LQFP • LC = 32-pin LQFP

2.4 Example

This is an example part number:

MC9S08PT60VQH

3 Parameter Classification

The electrical parameters shown in this supplement are guaranteed by various methods. To give the customer a better understanding, the following classification is used and the parameters are tagged accordingly in the tables where appropriate:

Table 1. Parameter Classifications

P	Those parameters are guaranteed during production testing on each individual device.
C	Those parameters are achieved by the design characterization by measuring a statistically relevant sample size across process variations.
T	Those parameters are achieved by design characterization on a small sample size from typical devices under typical conditions unless otherwise noted. All values shown in the typical column are within this category.
D	Those parameters are derived mainly from simulations.

NOTE

The classification is shown in the column labeled “C” in the parameter tables where appropriate.

Table 2. DC characteristics (continued)

Symbol	C	Descriptions		Min	Typical ¹	Max	Unit	
I _{OHT}	D	Output high current	Max total I _{OH} for all ports	5 V	—	—	-100	mA
				3 V	—	—	-50	
V _{OL}	P	Output low voltage	All I/O pins, standard-drive strength	5 V, I _{load} = 5 mA	—	—	0.8	V
	C			3 V, I _{load} = 2.5 mA	—	—	0.8	V
	P	High current drive pins, high-drive strength ²	5 V, I _{load} = 20 mA	—	—	0.8	V	
	C		3 V, I _{load} = 10 mA	—	—	0.8	V	
I _{OLT}	D	Output low current	Max total I _{OL} for all ports	5 V	—	—	100	mA
				3 V	—	—	50	
V _{IH}	P	Input high voltage	All digital inputs	V _{DD} > 4.5V	0.70 × V _{DD}	—	—	V
	C			V _{DD} > 2.7V	0.75 × V _{DD}	—	—	
V _{IL}	P	Input low voltage	All digital inputs	V _{DD} > 4.5V	—	—	0.30 × V _{DD}	V
	C			V _{DD} > 2.7V	—	—	0.35 × V _{DD}	
V _{hys}	C	Input hysteresis	All digital inputs	—	0.06 × V _{DD}	—	—	mV
I _{InI}	P	Input leakage current	All input only pins (per pin)	V _{IN} = V _{DD} or V _{SS}	—	0.1	1	μA
I _{OZI}	P	Hi-Z (off-state) leakage current	All input/output (per pin)	V _{IN} = V _{DD} or V _{SS}	—	0.1	1	μA
I _{OZTOTI}	C	Total leakage combined for all inputs and Hi-Z pins	All input only and I/O	V _{IN} = V _{DD} or V _{SS}	—	—	2	μA
R _{PU}	P	Pullup resistors	All digital inputs, when enabled (all I/O pins other than PTA2 and PTA3)	—	30.0	—	50.0	kΩ
R _{PU} ³	P	Pullup resistors	PTA2 and PTA3 pin	—	30.0	—	60.0	kΩ
I _{IC}	D	DC injection current ^{4, 5, 6}	Single pin limit	V _{IN} < V _{SS} , V _{IN} > V _{DD}	-0.2	—	2	mA
			Total MCU limit, includes sum of all stressed pins		-5	—	25	
C _{In}	C	Input capacitance, all pins		—	—	—	7	pF
V _{RAM}	C	RAM retention voltage		—	2.0	—	—	V

1. Typical values are measured at 25 °C. Characterized, not tested.
2. Only PTB4, PTB5, PTD0, PTD1, PTE0, PTE1, PTH0, and PTH1 support ultra high current output.
3. The specified resistor value is the actual value internal to the device. The pullup value may appear higher when measured externally on the pin.
4. All functional non-supply pins, except for PTA2 and PTA3, are internally clamped to V_{SS} and V_{DD}.
5. Input must be current-limited to the value specified. To determine the value of the required current-limiting resistor, calculate resistance values for positive and negative clamp voltages, then use the large one.

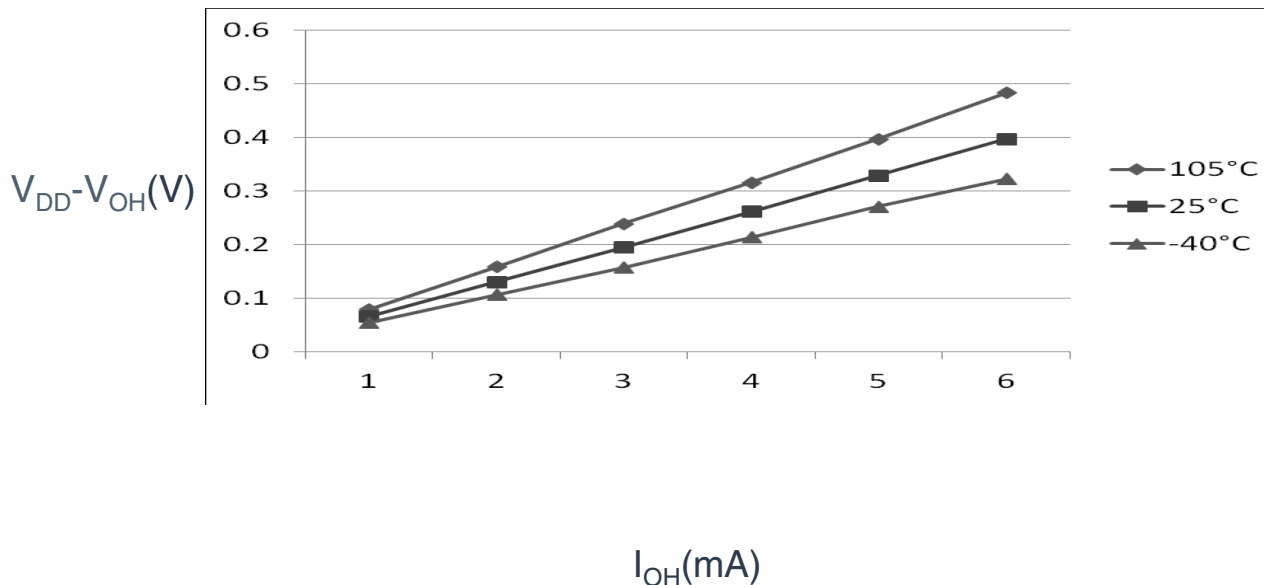


Figure 1. Typical I_{OH} Vs. V_{DD}-V_{OH} (standard drive strength) (V_{DD} = 5 V)

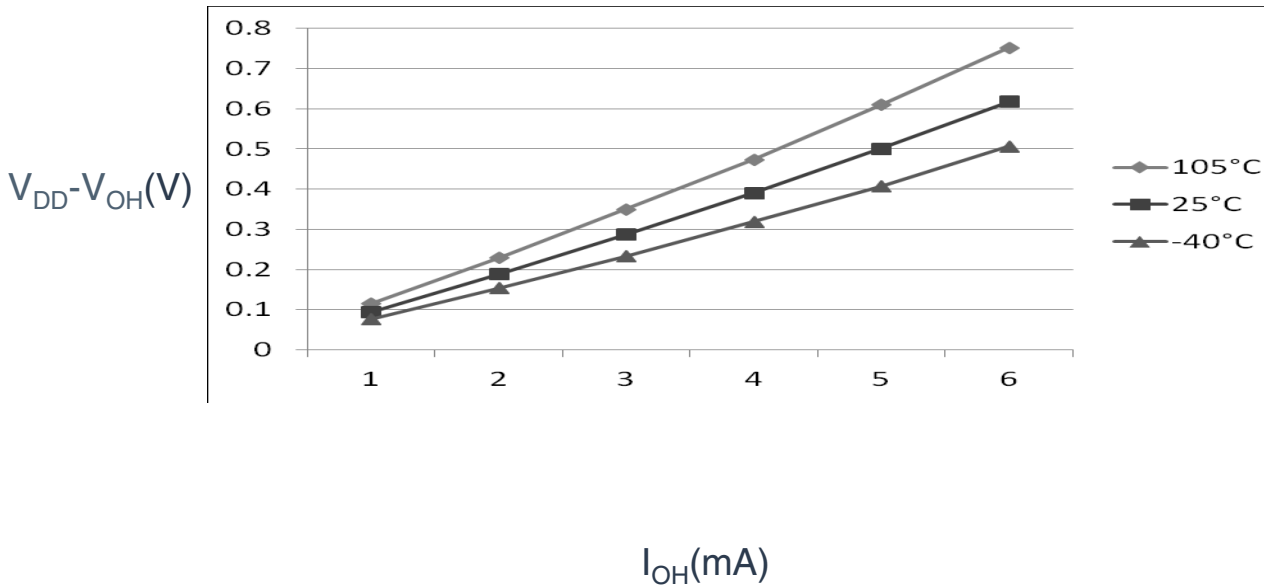


Figure 2. Typical I_{OH} Vs. V_{DD}-V_{OH} (standard drive strength) (V_{DD} = 3 V)

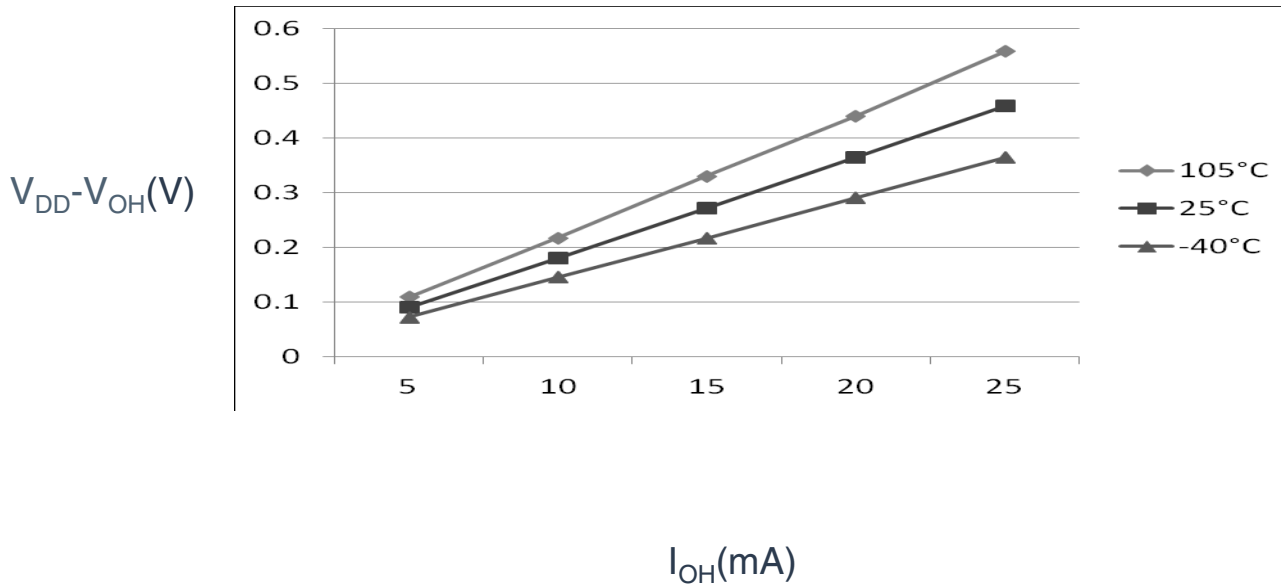


Figure 3. Typical I_{OH} Vs. $V_{DD}-V_{OH}$ (high drive strength) ($V_{DD} = 5\text{ V}$)

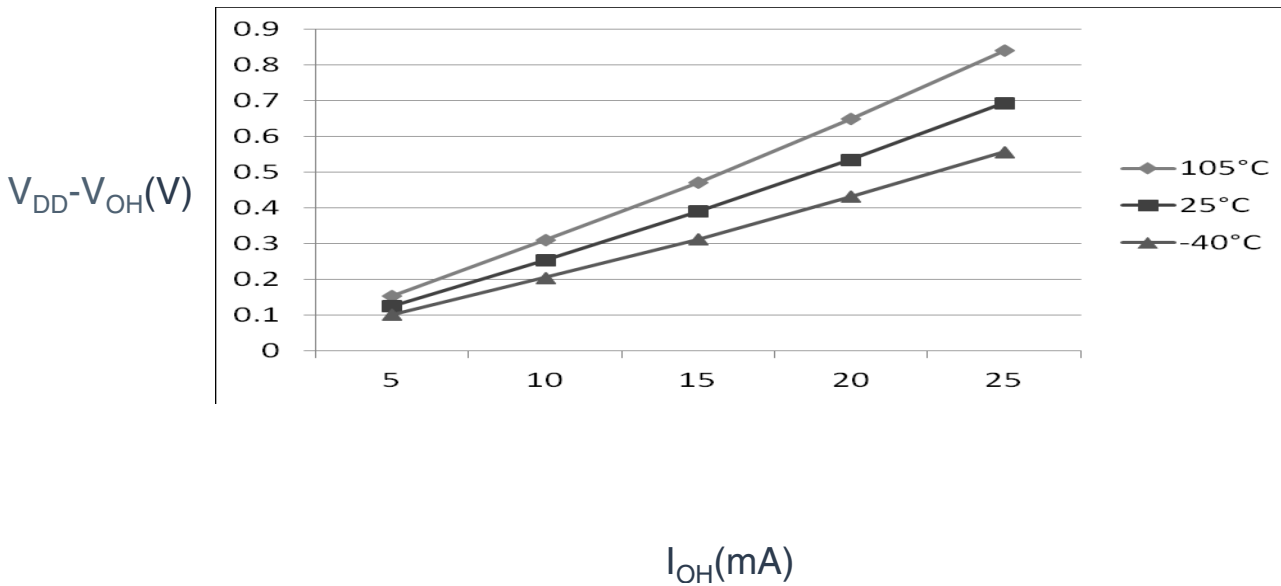


Figure 4. Typical I_{OH} Vs. $V_{DD}-V_{OH}$ (high drive strength) ($V_{DD} = 3\text{ V}$)

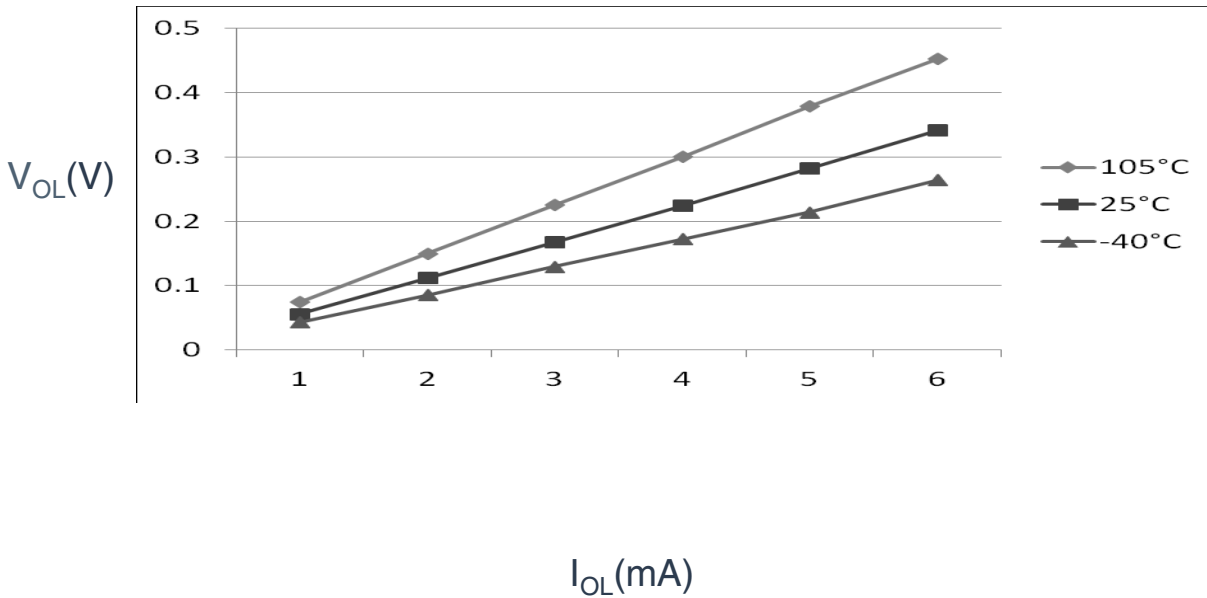


Figure 5. Typical I_{OL} Vs. V_{OL} (standard drive strength) ($V_{DD} = 5\text{ V}$)

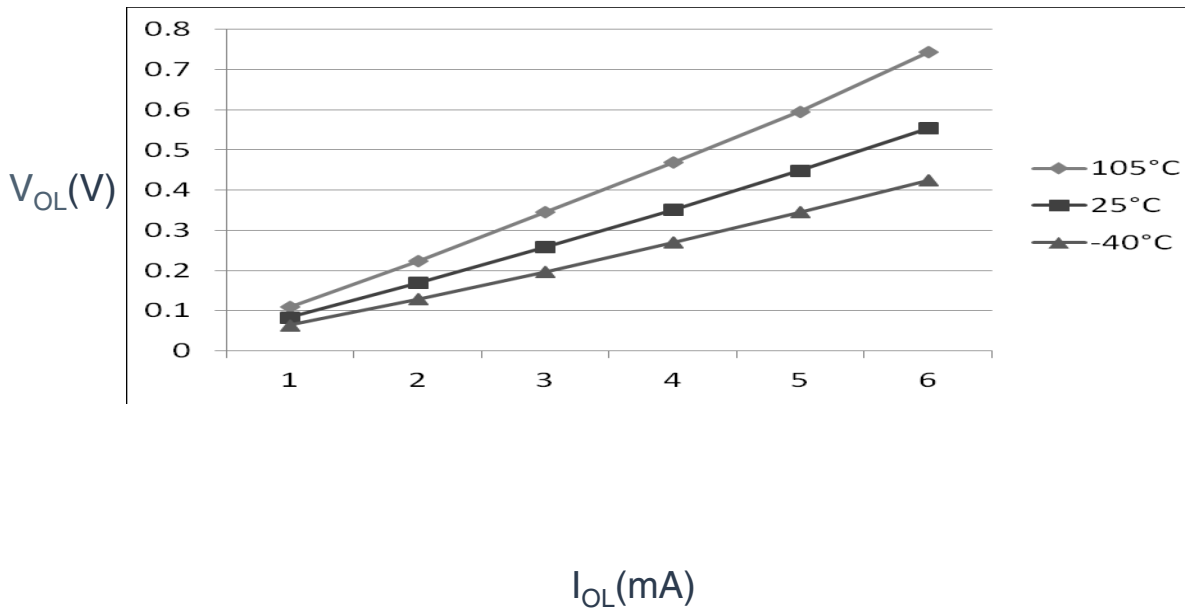


Figure 6. Typical I_{OL} Vs. V_{OL} (standard drive strength) ($V_{DD} = 3\text{ V}$)

5.1.2 Supply current characteristics

This section includes information about power supply current in various operating modes.

Table 4. Supply current characteristics

Num	C	Parameter	Symbol	Bus Freq	V _{DD} (V)	Typical ¹	Max	Unit	Temp
1	C	Run supply current FEI mode, all modules on; run from flash	R _I DD	20 MHz	5	12.6	—	mA	-40 to 105 °C
	C			10 MHz		7.2	—		
	C			1 MHz		2.4	—		
	C			20 MHz	3	9.6	—		
	C			10 MHz		6.1	—		
	C			1 MHz		2.1	—		
2	C	Run supply current FEI mode, all modules off & gated; run from flash	R _I DD	20 MHz	5	10.5	—	mA	-40 to 105 °C
	C			10 MHz		6.2	—		
	C			1 MHz		2.3	—		
	C			20 MHz	3	7.4	—		
	C			10 MHz		5.0	—		
	C			1 MHz		2.0	—		
3	P	Run supply current FBE mode, all modules on; run from RAM	R _I DD	20 MHz	5	12.1	14.8	mA	-40 to 105 °C
	C			10 MHz		6.5	—		
	C			1 MHz		1.8	—		
	P			20 MHz	3	9.1	11.8		
	C			10 MHz		5.5	—		
	C			1 MHz		1.5	—		
4	P	Run supply current FBE mode, all modules off & gated; run from RAM	R _I DD	20 MHz	5	9.8	12.3	mA	-40 to 105 °C
	C			10 MHz		5.4	—		
	C			1 MHz		1.6	—		
	P			20 MHz	3	6.9	9.2		
	C			10 MHz		4.4	—		
	C			1 MHz		1.4	—		
5	C	Wait mode current FEI mode, all modules on	W _I DD	20 MHz	5	7.8	—	mA	-40 to 105 °C
	C			10 MHz		4.5	—		
	C			1 MHz		1.3	—		
	C			20 MHz	3	5.1	—		
	C			10 MHz		3.5	—		
	C			1 MHz		1.2	—		
6	C	Stop3 mode supply current no clocks active (except 1 kHz LPO clock) ^{2,3}	S3 _I DD	—	5	3.8	—	μA	-40 to 105 °C
	C			—	3	3	—		-40 to 105 °C
7	C	ADC adder to stop3	—	—	5	44	—	μA	-40 to 105 °C

Table continues on the next page...

Table 4. Supply current characteristics (continued)

Num	C	Parameter	Symbol	Bus Freq	V _{DD} (V)	Typical ¹	Max	Unit	Temp
	C	ADLPC = 1 ADLSMP = 1 ADCO = 1 MODE = 10B ADICLK = 11B			3	40	—		
8	C	TSI adder to stop3 ⁴	—	—	5	111	—	μA	-40 to 105 °C
	C	PS = 010B NSCN = 0x0F EXTCHRG = 0 REFCHRG = 0 DVOLT = 01B			3	110	—		
9	C	LVD adder to stop3 ⁵	—	—	5	130	—	μA	-40 to 105 °C
	C				3	125	—		

1. Data in Typical column was characterized at 5.0 V, 25 °C or is typical recommended value.
2. RTC adder cause <1 μA I_{DD} increase typically, RTC clock source is 1 kHz LPO clock.
3. ACMP adder cause <10 μA I_{DD} increase typically.
4. The current varies with TSI configuration and capacity of touch electrode. Please refer to [TSI electrical specifications](#).
5. LVD is periodically woken up from stop3 by 5% duty cycle. The period is equal to or less than 2 ms.

5.1.3 EMC performance

Electromagnetic compatibility (EMC) performance is highly dependent on the environment in which the MCU resides. Board design and layout, circuit topology choices, location and characteristics of external components as well as MCU software operation all play a significant role in EMC performance. The system designer should consult Freescale applications notes such as [AN2321](#), [AN1050](#), [AN1263](#), [AN2764](#), and [AN1259](#) for advice and guidance specifically targeted at optimizing EMC performance.

5.1.3.1 EMC radiated emissions operating behaviors

Table 5. EMC radiated emissions operating behaviors for 64-pin SOIC package

Symbol	Description	Frequency band (MHz)	Typ.	Unit	Notes
V _{RE1}	Radiated emissions voltage, band 1	0.15–50	12	dBμV	1, 2
V _{RE2}	Radiated emissions voltage, band 2	50–150	10		
V _{RE3}	Radiated emissions voltage, band 3	150–500	4		
V _{RE4}	Radiated emissions voltage, band 4	500–1000	5		
V _{RE_IEC}	IEC level	0.15–1000	N	—	2, 3

Switching specifications

1. Determined according to IEC Standard 61967-1, *Integrated Circuits - Measurement of Electromagnetic Emissions, 150 kHz to 1 GHz Part 1: General Conditions and Definitions* and IEC Standard 61967-2, *Integrated Circuits - Measurement of Electromagnetic Emissions, 150 kHz to 1 GHz Part 2: Measurement of Radiated Emissions—TEM Cell and Wideband TEM Cell Method*. Measurements were made while the microcontroller was running basic application code. The reported emission level is the value of the maximum measured emission, rounded up to the next whole number, from among the measured orientations in each frequency range.
2. $V_{DD} = 5.0\text{ V}$, $T_A = 25\text{ °C}$, $f_{OSC} = 10\text{ MHz}$ (crystal), $f_{SYS} = 20\text{ MHz}$, $f_{BUS} = 20\text{ MHz}$
3. Specified according to Annex D of IEC Standard 61967-2, *Measurement of Radiated Emissions—TEM Cell and Wideband TEM Cell Method*

5.2 Switching specifications

5.2.1 Control timing

Table 6. Control timing

Num	C	Rating	Symbol	Min	Typical ¹	Max	Unit	
1	P	Bus frequency ($t_{cyc} = 1/f_{Bus}$)	f_{Bus}	DC	—	20	MHz	
2	P	Internal low power oscillator frequency	f_{LPO}	0.67	1.0	1.25	KHz	
3	D	External reset pulse width ²	t_{extrst}	$1.5 \times t_{cyc}$	—	—	ns	
4	D	Reset low drive	t_{rstdrv}	$34 \times t_{cyc}$	—	—	ns	
5	D	BKGD/MS setup time after issuing background debug force reset to enter user or BDM modes	t_{MSSU}	500	—	—	ns	
6	D	BKGD/MS hold time after issuing background debug force reset to enter user or BDM modes ³	t_{MSH}	100	—	—	ns	
7	D	IRQ pulse width	Asynchronous path ²	t_{LIH}	100	—	—	ns
	D		Synchronous path ⁴	t_{HIL}	$1.5 \times t_{cyc}$	—	—	ns
8	D	Keyboard interrupt pulse width	Asynchronous path ²	t_{LIH}	100	—	—	ns
	D		Synchronous path	t_{HIL}	$1.5 \times t_{cyc}$	—	—	ns
9	C	Port rise and fall time - standard drive strength (load = 50 pF) ⁵	—	t_{Rise}	—	10.2	—	ns
	C		—	t_{Fall}	—	9.5	—	ns
	C	Port rise and fall time - high drive strength (load = 50 pF) ⁵	—	t_{Rise}	—	5.4	—	ns
	C		—	t_{Fall}	—	4.6	—	ns

1. Typical values are based on characterization data at $V_{DD} = 5.0\text{ V}$, 25 °C unless otherwise stated.
2. This is the shortest pulse that is guaranteed to be recognized as a reset pin request.
3. To enter BDM mode following a POR, BKGD/MS must be held low during the powerup and for a hold time of t_{MSH} after V_{DD} rises above V_{LVD} .
4. This is the minimum pulse width that is guaranteed to pass through the pin synchronization circuitry. Shorter pulses may or may not be recognized. In stop mode, the synchronizer is bypassed so shorter pulses can be recognized.
5. Timing is shown with respect to 20% V_{DD} and 80% V_{DD} levels in operating temperature range.

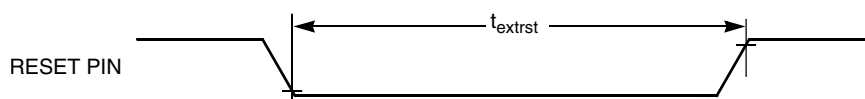


Figure 9. Reset timing

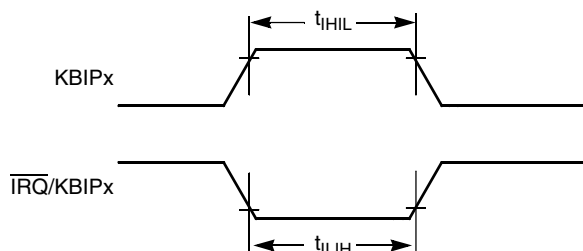


Figure 10. IRQ/KBIPx timing

5.2.2 Debug trace timing specifications

Table 7. Debug trace operating behaviors

Symbol	Description	Min.	Max.	Unit
t_{cyc}	Clock period	Frequency dependent		MHz
t_{wl}	Low pulse width	2	—	ns
t_{wh}	High pulse width	2	—	ns
t_r	Clock and data rise time	—	3	ns
t_f	Clock and data fall time	—	3	ns
t_s	Data setup	3	—	ns
t_h	Data hold	2	—	ns

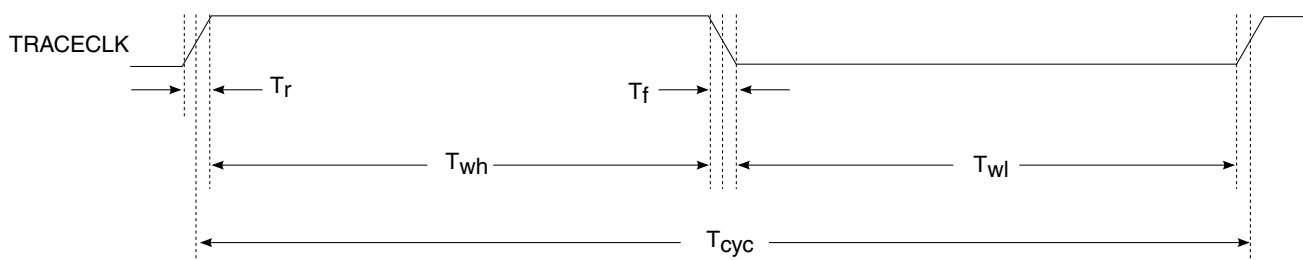


Figure 11. TRACE_CLKOUT specifications

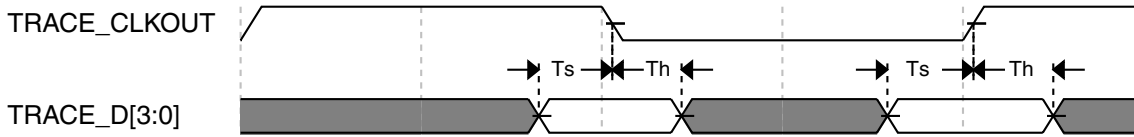


Figure 12. Trace data specifications

5.2.3 FTM module timing

Synchronizer circuits determine the shortest input pulses that can be recognized or the fastest clock that can be used as the optional external source to the timer counter. These synchronizers operate from the current bus rate clock.

Table 8. FTM input timing

No.	C	Function	Symbol	Min	Max	Unit
1	D	External clock frequency	f_{TCLK}	0	$f_{Bus}/4$	Hz
2	D	External clock period	t_{TCLK}	4	—	t_{cyc}
3	D	External clock high time	t_{clkh}	1.5	—	t_{cyc}
4	D	External clock low time	t_{clkl}	1.5	—	t_{cyc}
5	D	Input capture pulse width	t_{iCPW}	1.5	—	t_{cyc}

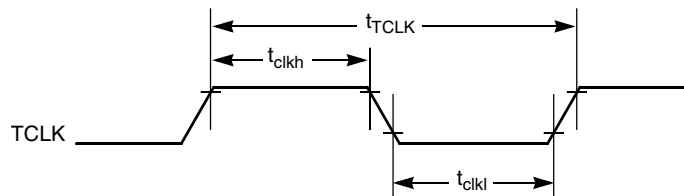


Figure 13. Timer external clock

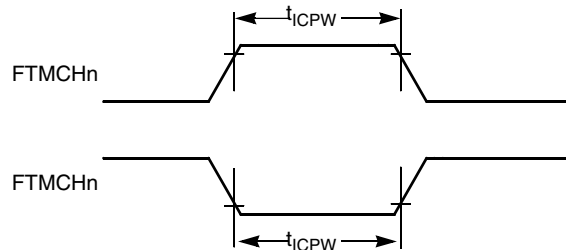


Figure 14. Timer input capture pulse

5.3 Thermal specifications

5.3.1 Thermal operating requirements

Table 9. Thermal operating requirements

Symbol	Description	Min.	Max.	Unit
T_J	Die junction temperature	-40	125	°C
T_A	Ambient temperature	-40	105	°C

NOTE

Maximum T_A can be exceeded only if the user ensures that T_J does not exceed the maximum. The simplest method to determine T_J is: $T_J = T_A + R_{\theta JA} \times \text{chip power dissipation}$.

5.3.2 Thermal characteristics

This section provides information about operating temperature range, power dissipation, and package thermal resistance. Power dissipation on I/O pins is usually small compared to the power dissipation in on-chip logic and voltage regulator circuits, and it is user-determined rather than being controlled by the MCU design. To take $P_{I/O}$ into account in power calculations, determine the difference between actual pin voltage and V_{SS} or V_{DD} and multiply by the pin current for each I/O pin. Except in cases of unusually high pin current (heavy loads), the difference between pin voltage and V_{SS} or V_{DD} will be very small.

Table 10. Thermal attributes

Board type	Symbol	Description	64 LQFP	64 QFP	48 LQFP	44 LQFP	32 LQFP	Unit	Notes
Single-layer (1S)	$R_{\theta JA}$	Thermal resistance, junction to ambient (natural convection)	71	61	81	75	86	°C/W	1, 2
Four-layer (2s2p)	$R_{\theta JA}$	Thermal resistance, junction to ambient (natural convection)	53	47	57	53	57	°C/W	1, 3
Single-layer (1S)	$R_{\theta JMA}$	Thermal resistance, junction to ambient (200 ft./min. air speed)	59	50	68	62	72	°C/W	1, 3
Four-layer (2s2p)	$R_{\theta JMA}$	Thermal resistance, junction to ambient (200 ft./min. air speed)	46	41	50	47	51	°C/W	1, 3

Table continues on the next page...

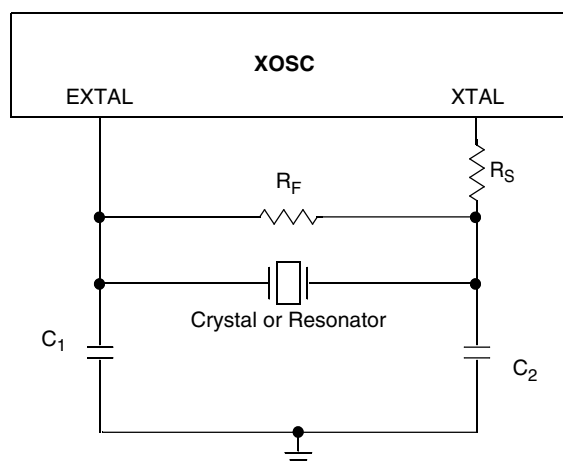


Figure 15. Typical crystal or resonator circuit

6.2 NVM specifications

This section provides details about program/erase times and program/erase endurance for the flash and EEPROM memories.

Table 12. Flash characteristics

C	Characteristic	Symbol	Min ¹	Typical ²	Max ³	Unit ⁴
D	Supply voltage for program/erase -40 °C to 105 °C	$V_{\text{prog/erase}}$	2.7	—	5.5	V
D	Supply voltage for read operation	V_{Read}	2.7	—	5.5	V
D	NVM Bus frequency	f_{NVMBUS}	1	—	25	MHz
D	NVM Operating frequency	f_{NVMOP}	0.8	1	1.05	MHz
D	Erase Verify All Blocks	t_{VFYALL}	—	—	17338	t_{cyc}
D	Erase Verify Flash Block	t_{RD1BLK}	—	—	16913	t_{cyc}
D	Erase Verify EEPROM Block	t_{RD1BLK}	—	—	810	t_{cyc}
D	Erase Verify Flash Section	t_{RD1SEC}	—	—	484	t_{cyc}
D	Erase Verify EEPROM Section	t_{DRD1SEC}	—	—	555	t_{cyc}
D	Read Once	t_{RDONCE}	—	—	450	t_{cyc}
D	Program Flash (2 word)	t_{PGM2}	0.12	0.12	0.29	ms
D	Program Flash (4 word)	t_{PGM4}	0.20	0.21	0.46	ms
D	Program Once	t_{PGMONCE}	0.20	0.21	0.21	ms
D	Program EEPROM (1 Byte)	t_{DPGM1}	0.10	0.10	0.27	ms
D	Program EEPROM (2 Byte)	t_{DPGM2}	0.17	0.18	0.43	ms
D	Program EEPROM (3 Byte)	t_{DPGM3}	0.25	0.26	0.60	ms
D	Program EEPROM (4 Byte)	t_{DPGM4}	0.32	0.33	0.77	ms
D	Erase All Blocks	t_{ERSALL}	96.01	100.78	101.49	ms
D	Erase Flash Block	t_{ERSBLK}	95.98	100.75	101.44	ms

Table continues on the next page...

Table 13. 5 V 12-bit ADC operating conditions (continued)

Characteristic	Conditions	Symb	Min	Typ ¹	Max	Unit	Comment
	10-bit mode		—	—	5		
	<ul style="list-style-type: none"> $f_{ADCK} > 4$ MHz $f_{ADCK} < 4$ MHz 		—	—	10		
	8-bit mode (all valid f_{ADCK})		—	—	10		
ADC conversion clock frequency	High speed (ADLPC=0)	f_{ADCK}	0.4	—	8.0	MHz	—
	Low power (ADLPC=1)		0.4	—	4.0		

1. Typical values assume $V_{DDA} = 5.0$ V, Temp = 25°C, $f_{ADCK}=1.0$ MHz unless otherwise stated. Typical values are for reference only and are not tested in production.
2. DC potential difference.

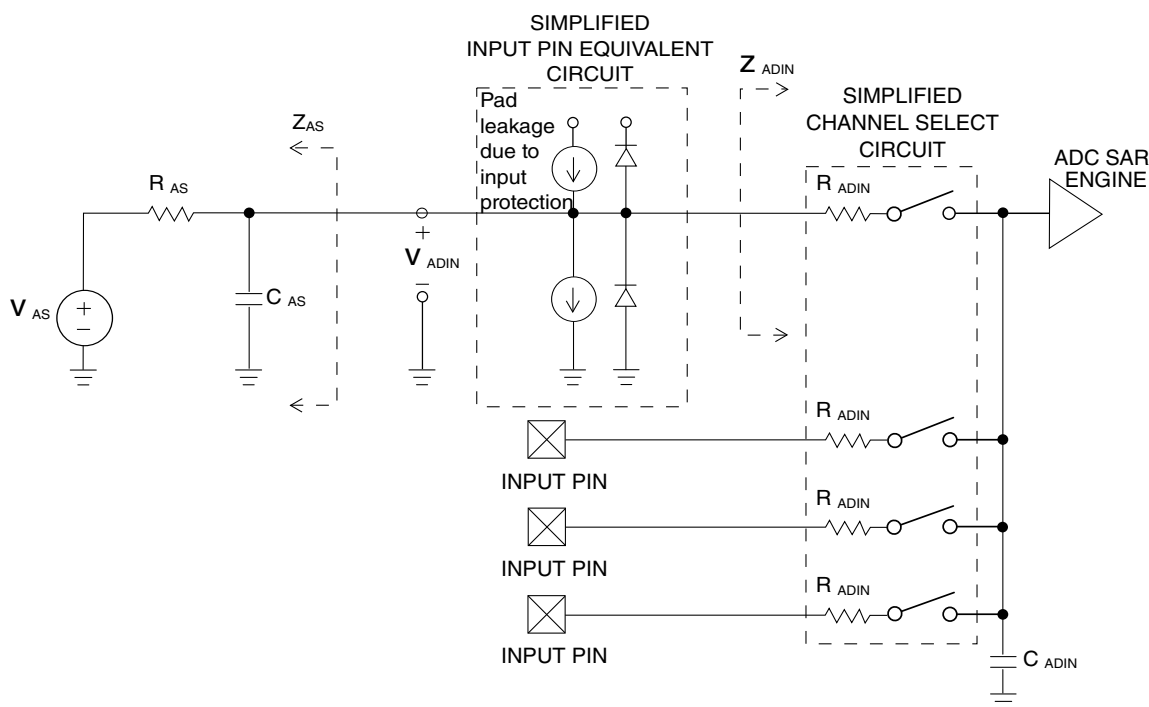


Figure 16. ADC input impedance equivalency diagram

Table 14. 12-bit ADC Characteristics ($V_{REFH} = V_{DDA}$, $V_{REFL} = V_{SSA}$)

Characteristic	Conditions	C	Symb	Min	Typ ¹	Max	Unit
Supply current		T	I_{DDA}	—	133	—	μ A
ADLPC = 1							
ADLSMP = 1							
ADCO = 1							
Supply current		T	I_{DDA}	—	218	—	μ A

Table continues on the next page...

Table 14. 12-bit ADC Characteristics ($V_{REFH} = V_{DDA}$, $V_{REFL} = V_{SSA}$) (continued)

Characteristic	Conditions	C	Symb	Min	Typ ¹	Max	Unit
Input leakage error ⁷	all modes	D	E_{IL}	$I_{in} * R_{AS}$			mV
Temp sensor slope	-40°C– 25°C	D	m	—	3.266	—	mV/°C
	25°C– 125°C			—	3.638	—	
Temp sensor voltage	25°C	D	V_{TEMP25}	—	1.396	—	V

1. Typical values assume $V_{DDA} = 5.0$ V, Temp = 25°C, $f_{ADCK} = 1.0$ MHz unless otherwise stated. Typical values are for reference only and are not tested in production.
2. Includes quantization.
3. $1 \text{ LSB} = (V_{REFH} - V_{REFL})/2^N$
4. Monotonicity and no-missing-codes guaranteed in 10-bit and 8-bit modes
5. $V_{ADIN} = V_{SSA}$
6. $V_{ADIN} = V_{DDA}$
7. I_{in} = leakage current (refer to DC characteristics)

6.3.2 Analog comparator (ACMP) electricals

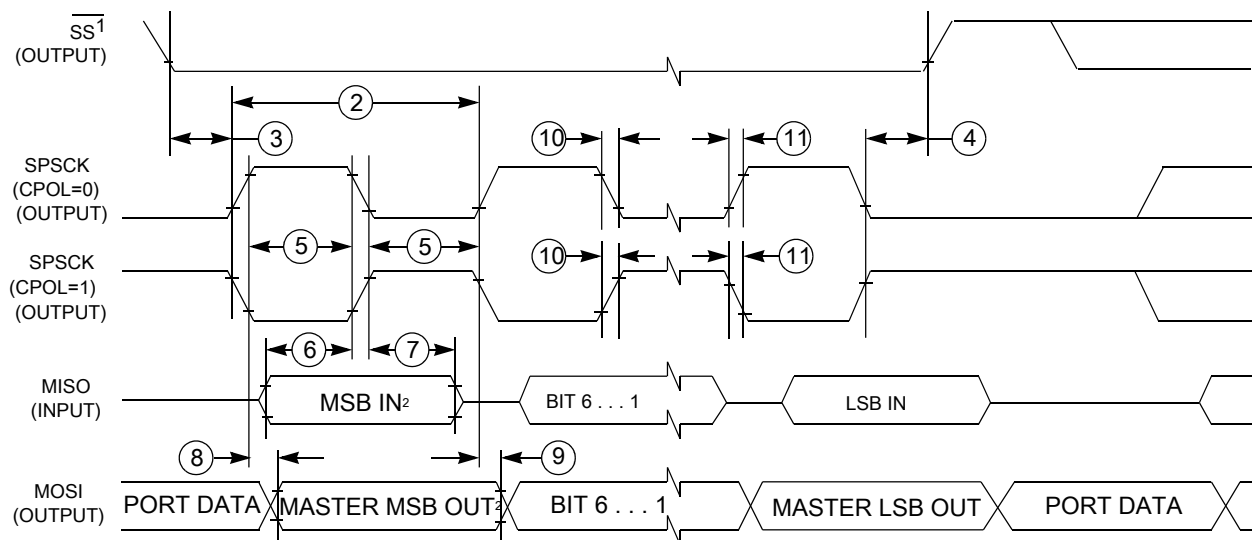
Table 15. Comparator electrical specifications

C	Characteristic	Symbol	Min	Typical	Max	Unit
D	Supply voltage	V_{DDA}	2.7	—	5.5	V
T	Supply current (Operation mode)	I_{DDA}	—	10	20	μ A
D	Analog input voltage	V_{AIN}	$V_{SS} - 0.3$	—	V_{DDA}	V
P	Analog input offset voltage	V_{AIO}	—	—	40	mV
C	Analog comparator hysteresis (HYST=0)	V_H	—	15	20	mV
C	Analog comparator hysteresis (HYST=1)	V_H	—	20	30	mV
T	Supply current (Off mode)	I_{DDAOFF}	—	60	—	nA
C	Propagation Delay	t_D	—	0.4	1	μ s

6.4 Communication interfaces

6.4.1 SPI switching specifications

The serial peripheral interface (SPI) provides a synchronous serial bus with master and slave operations. Many of the transfer attributes are programmable. The following tables provide timing characteristics for classic SPI timing modes. Refer to the SPI chapter of the chip's reference manual for information about the modified transfer formats used for



- 1. If configured as output
- 2. LSBF = 0. For LSBF = 1, bit order is LSB, bit 1, ..., bit 6, MSB.

Figure 18. SPI master mode timing (CPHA=1)

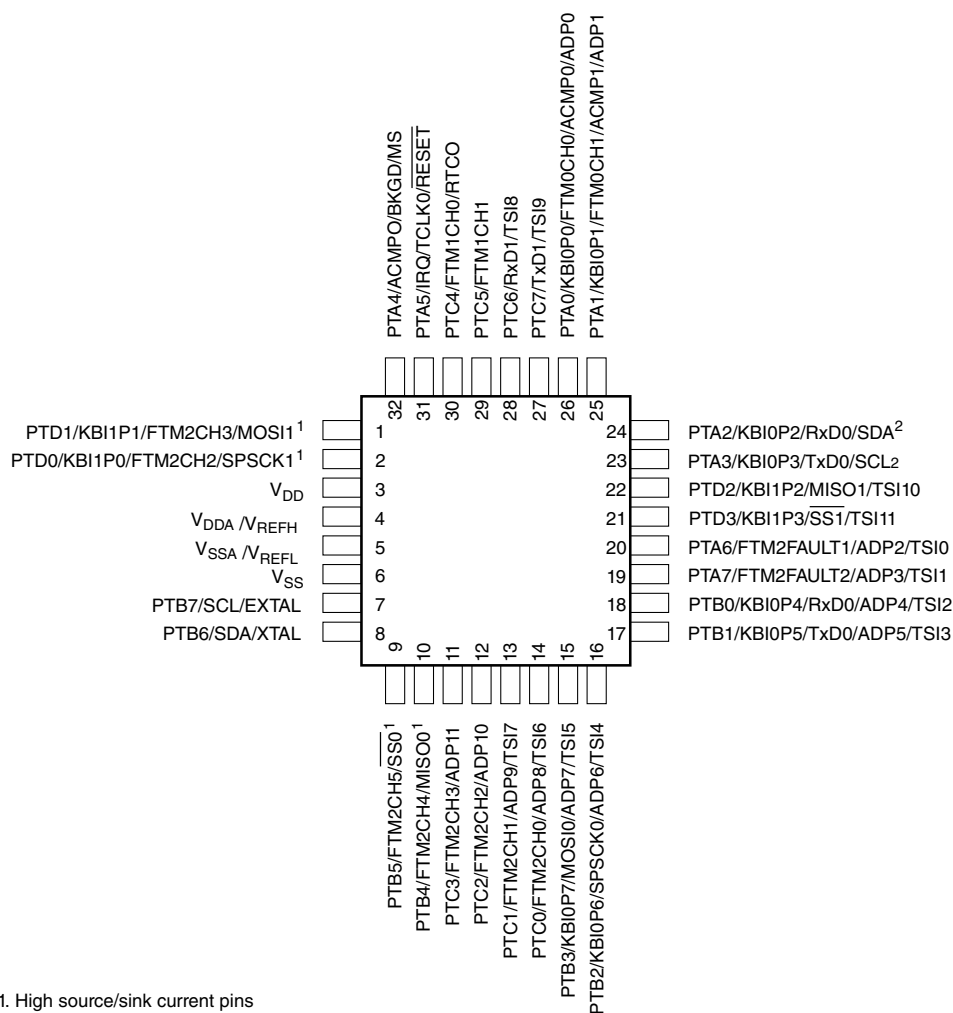
Table 17. SPI slave mode timing

Nu m.	Symbol	Description	Min.	Max.	Unit	Comment
1	f_{op}	Frequency of operation	0	$f_{BUS}/4$	Hz	f_{BUS} is the bus clock as defined in .
2	t_{SPSCCK}	SPSCCK period	$4 \times t_{BUS}$	—	ns	$t_{BUS} = 1/f_{BUS}$
3	t_{Lead}	Enable lead time	1	—	t_{BUS}	—
4	t_{Lag}	Enable lag time	1	—	t_{BUS}	—
5	$t_{WSPSCCK}$	Clock (SPSCCK) high or low time	$t_{BUS} - 30$	—	ns	—
6	t_{SU}	Data setup time (inputs)	15	—	ns	—
7	t_{HI}	Data hold time (inputs)	25	—	ns	—
8	t_a	Slave access time	—	t_{BUS}	ns	Time to data active from high-impedance state
9	t_{dis}	Slave MISO disable time	—	t_{BUS}	ns	Hold time to high-impedance state
10	t_v	Data valid (after SPSCCK edge)	—	25	ns	—
11	t_{HO}	Data hold time (outputs)	0	—	ns	—
12	t_{RI}	Rise time input	—	$t_{BUS} - 25$	ns	—
	t_{FI}	Fall time input	—			
13	t_{RO}	Rise time output	—	25	ns	—
	t_{FO}	Fall time output	—			

Table 19. Pin availability by package pin-count

Pin Number				Lowest Priority <-- --> Highest				
64-LQFP 64-QFP	48-LQFP	44-LQFP	32-LQFP	Port Pin	Alt 1	Alt 2	Alt 3	Alt 4
1	1	1	1	PTD1 ¹	KBI1P1	FTM2CH3	MOSI1	—
2	2	2	2	PTD0 ¹	KBI1P0	FTM2CH2	SPSCK1	—
3	—	—	—	PTH7	—	—	—	—
4	—	—	—	PTH6	—	—	—	—
5	3	3	—	PTE7	—	TCLK2	—	—
6	4	4	—	PTH2	—	BUSOUT	—	—
7	5	5	3	—	—	—	—	V _{DD}
8	6	6	4	—	—	—	V _{DDA}	V _{REFH}
9	7	7	5	—	—	—	V _{SSA}	V _{REFL}
10	8	8	6	—	—	—	—	V _{SS}
11	9	9	7	PTB7	—	SCL	—	EXTAL
12	10	10	8	PTB6	—	SDA	—	XTAL
13	11	11	—	—	—	—	—	V _{SS}
14	—	—	—	PTH1 ¹	—	FTM2CH1	—	—
15	—	—	—	PTH0 ¹	—	FTM2CH0	—	—
16	12	—	—	PTE6	—	—	—	—
17	13	—	—	PTE5	—	—	—	—
18	14	12	9	PTB5 ¹	FTM2CH5	$\overline{SS0}$	—	—
19	15	13	10	PTB4 ¹	FTM2CH4	MISO0	—	—
20	16	14	11	PTC3	FTM2CH3	—	ADP11	—
21	17	15	12	PTC2	FTM2CH2	—	ADP10	—
22	18	16	—	PTD7	KBI1P7	TXD2	—	—
23	19	17	—	PTD6	KBI1P6	RXD2	—	—
24	20	18	—	PTD5	KBI1P5	—	—	—
25	21	19	13	PTC1	—	FTM2CH1	ADP9	TSI7
26	22	20	14	PTC0	—	FTM2CH0	ADP8	TSI6
27	—	—	—	PTF7	—	—	ADP15	—
28	—	—	—	PTF6	—	—	ADP14	—
29	—	—	—	PTF5	—	—	ADP13	—
30	—	—	—	PTF4	—	—	ADP12	—
31	23	21	15	PTB3	KBI0P7	MOSI0	ADP7	TSI5
32	24	22	16	PTB2	KBI0P6	SPSCK0	ADP6	TSI4
33	25	23	17	PTB1	KBI0P5	TXD0	ADP5	TSI3
34	26	24	18	PTB0	KBI0P4	RXD0	ADP4	TSI2
35	—	—	—	PTF3	—	—	—	TSI15
36	—	—	—	PTF2	—	—	—	TSI14
37	27	25	19	PTA7	FTM2FAULT2	—	ADP3	TSI1

Table continues on the next page...



- 1. High source/sink current pins
- 2. True open drain pins

Figure 24. MC9S08PT60 32-pin LQFP package

9 Revision history

The following table provides a revision history for this document.

Table 20. Revision history

Rev. No.	Date	Substantial Changes
1	10/2011	Initial public revision.
2	11/2011	<ul style="list-style-type: none"> • Updated some TBDs • Updated LVD and POR data • Updated ADC data • Updated SPI data • Updated TSI data.
3	4/2012	<ul style="list-style-type: none"> • Finished all the TBDs • Updated package information
4	09/2014	<ul style="list-style-type: none"> • Updated V_{HBM} in ESD handling ratings

Table continues on the next page...



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